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(54) **SEMICONDUCTOR ASSEMBLIES INCLUDING COMBINATION MEMORY AND METHODS OF MANUFACTURING THE SAME**

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ABSTRACT

Semiconductor devices including vertically-stacked combination memory devices and associated systems and methods are disclosed herein. The vertically-stacked combination memory devices include at least one volatile memory die and at least one non-volatile memory die stacked on top of each other. The corresponding stack may be attached to a controller die that is configured to provide interface for the attached volatile and non-volatile memory dies.

